



L-53P3C

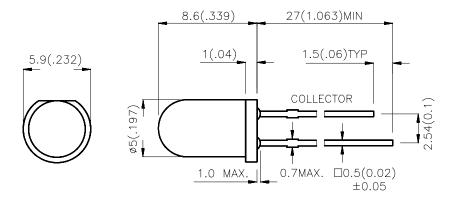
Features

- •MECHANICALLY AND SPECTRALLY MATCHED TO THE L-53 SERIES INFRARED EMITTING LED LAMP.
- •WATER CLEAR LENS.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
- 3. Lead spacing is measured where the lead emerge package.
- 4. Specifications are subject to change without notice.

SPEC NO: DSAA4158 REV NO: V.4
APPROVED: J. Lu CHECKED: Allen Liu

DATE:MAR/06/2003 DRAWN: D.L.HUANG PAGE: 1 OF 2



Electrical / Optical Characteristics at T_A=25°C

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Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Condiction
VBR CEO	Collector-to-Emitter Breakdown Voltage	30	-	-	V	Ic=100uA E _e =0mW/cm ²
VBR ECO	Emitter-to-Collector Breakdown Voltage	5	-	-	V	I _E =100uA E _e =0mW/cm ²
VCE (SAT)	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	Ic=2mA E _e =20mW/cm ²
lceo	Collector Dark Current	-	-	100	nA	Vc=10V E _e =0mW/cm ²
Tr	Rise Time (10% to 90%)	-	3	-	us	V _{CE} =5V lc=1mA RL=1000Ω
TF	Fall Time (90% to 10%)	-	3	-	us	
I (ON)	On State Collector Current	0.1	0.5	-	mA	V _{CE} =5V Ee=1mW/cm ² λ=940nm

Absolute Maximum Ratings at T_A =25°C

Parameter	Maximum Rating		
Collector-to-Emitter Breakdown Voltage	30V		
Emitter-to-Collector Breakdown Voltage	5V		
Power Dissipation at (or below) 25°C Free Air Temperature	100mW		
Operating Temperature Range	-40°C ~ +85°C		
Storage Temperature Range	-40°C ~ +85°C		
Lead soldering Temperature (>5mm for 5sec)	260°C		

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